ASZD010170C

1700V, 10A Silicon Carbide Schottky Diode

Features

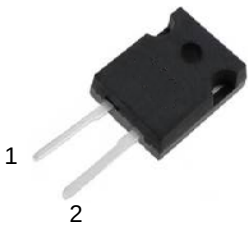
- Low reverse current
- Good surge current capability
- Low capacitive charge
- No reverse recovery current
- Halogen free, RoHs compliant

V_{RRM}	=	1700	V
I_F (T_C=164℃)	=	10	A
Q_C	=	114	nC

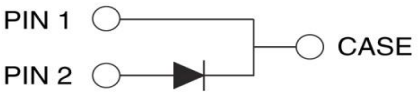
Benefits

- System efficiency improvement over Si diodes
- Higher switching frequency
- Increased power density
- Essentially no switching losses

Package



TO-247-2



Applications

- Switch mode power supplies (SMPS)
- Uninterruptible power supplies
- On Board Charger
- UPS

Part Number	Package	Marking
ASZD010170C	TO-247-2	ASZD010170C

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1700V, 10A Silicon Carbide Schottky Diode

Maximum Ratings(T_C =25℃,unless other wise specified)

Symbol	Parameter	Test conditions	Value	Unit
V_{RRM}	Repetitive peak reverse voltage		1700	V
V_{RSM}	Non-repetitive peak reverse voltage		1700	V
I_F	Continuous forward current	T_C=25°C T_C=135°C T_C=165°C	51 24 10	A
I_{FRM}	Repetitive forward surge current	T_C=25°C , t_p=10ms, Half Sine Pulse T_C=110°C , t_p=10ms, Half Sine Pulse	45 25	A
I_{FSM}	Non-Repetitive forward surge current	T_C=25°C , t_p=10ms, Half Sine Pulse T_C=110°C , t_p=10ms, Half Sine Pulse	105 90	A
$\int i^2dt$	i^2t value	T_C=25°C , t_p=10ms, Half Sine Pulse T_C=110°C , t_p=10ms, Half Sine Pulse	55 24	A^2S
P_{tot}	Power dissipation	T_C=25°C T_C=110°C	242 105	W
T_j	Operating junction temperature		-55~175	°C
T_{stg}	Storage temperature		-55~175	°C

Electrical Characteristics(T_j =25℃,unless other wise specified)

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
V_{DC}	DC blocking voltage	T_j=25°C	1700			V
V_F	Diode forward voltage	I_F=10A T_j=25°C I_F=10A T_j=175°C		1.25 1.55	1.6	V
I_R	Reverse current	V_R=1700V T_j=25°C V_R=1700V T_j=175°C		3 32	30 150	μA
Q_C	Total capactive charge	V_R=1000V T_j=25°C $Q_C = \int_0^{VR} C(V)dV$		114		nC
C	Total capacitance	V_R=0V f=1MHz V_R=800V f=1MHz V_R=1000V f=1MHz		2403 65 59		pF

Thermal Characteristics

Symbol	Parameter	Value			Unit
		Min.	Typ.	Max.	
$R_{th(jc)}$	Thermal resistance from junction to case		0.62		°C/W

Typical Performance

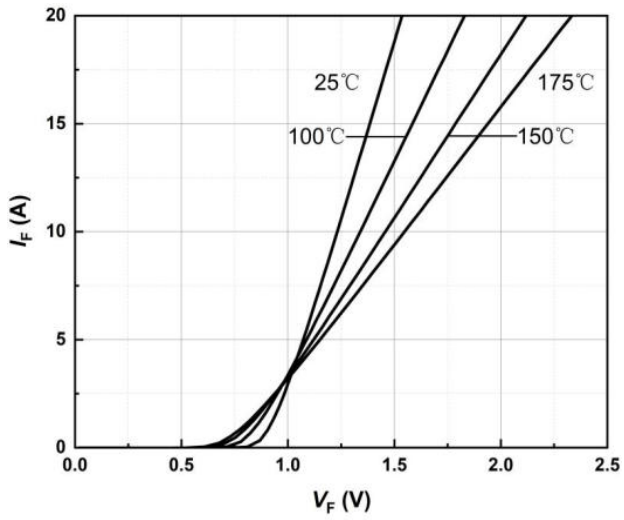

Figure 1. Typical forward characteristics

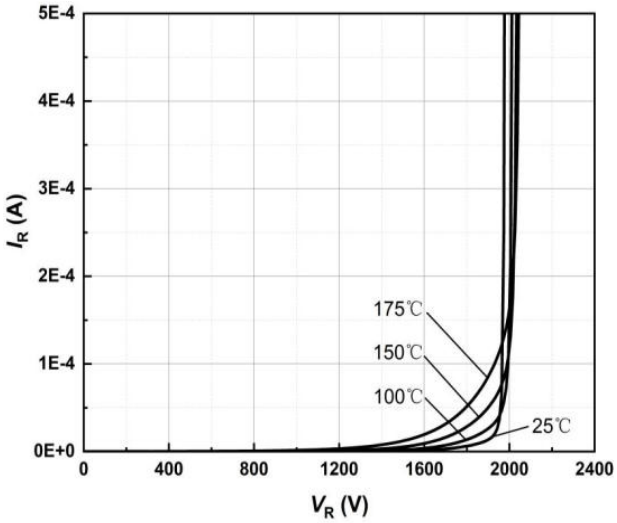

Figure 2. Typical reverse current as function of reverse voltage

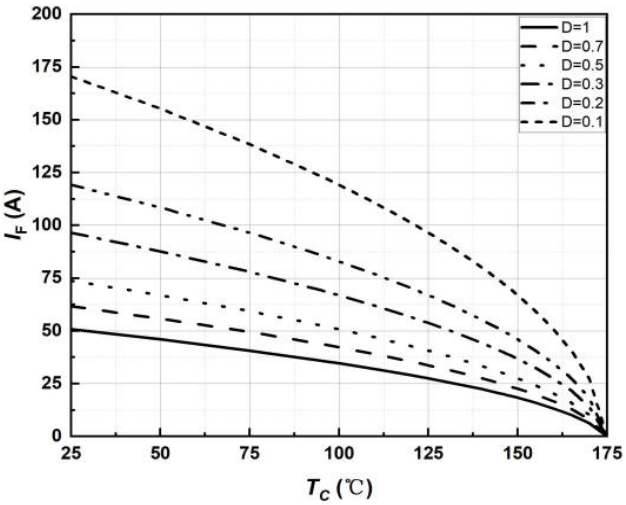

Figure 3. Diode forward current as function of temperature, D=duty cycle

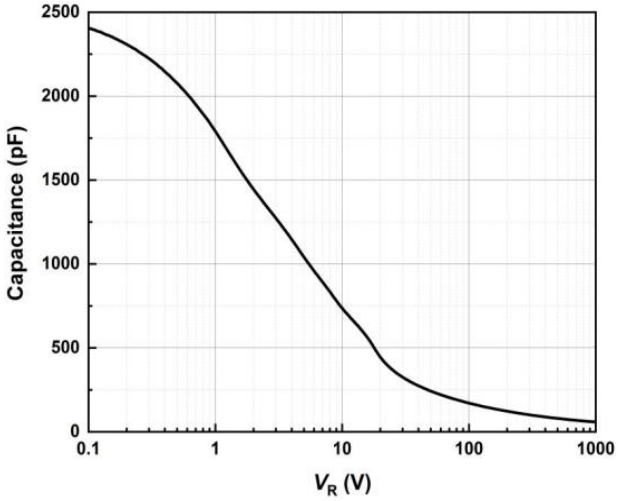

Figure 4. Typical capacitance as function of reverse voltage, $C=f(V_R)$; $T_j=25°C$

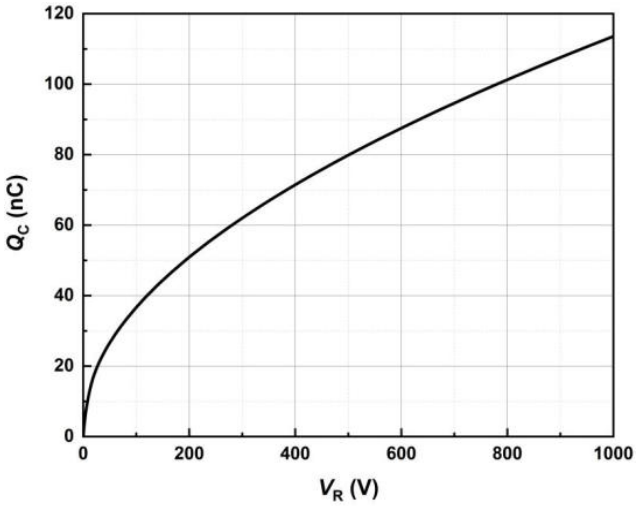

Figure 5. Typical reverse charge as function of reverse voltage

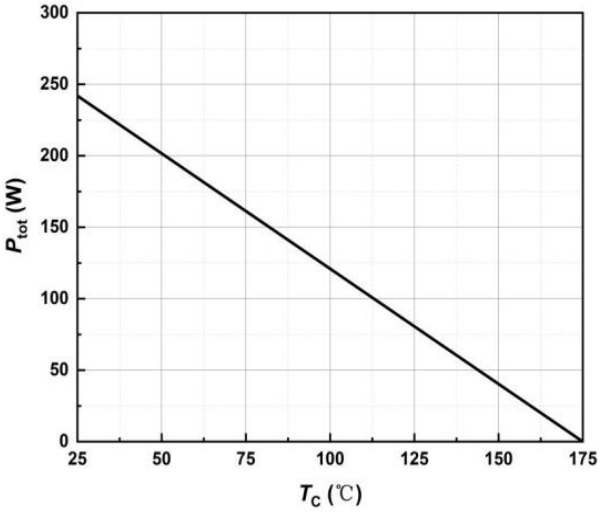

Figure 6. Power dissipation as function of case temperature

Typical Performance

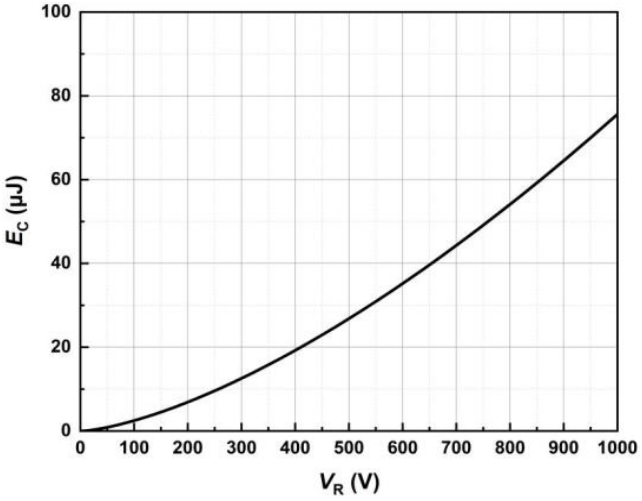

Figure 7.Capacitance stored energy

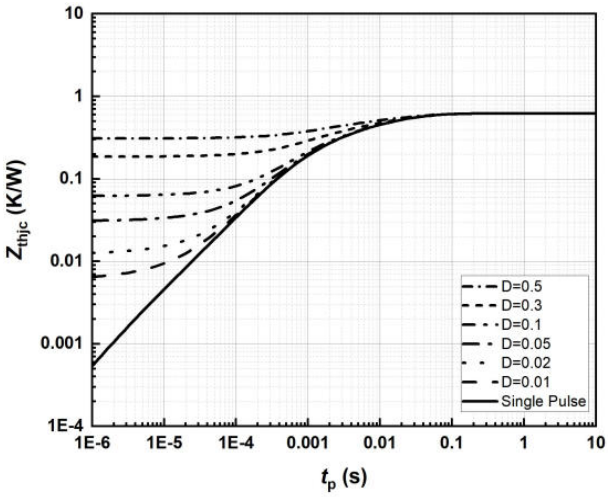

Figure 8. Max. transient thermal impedance

TO-247-2 Package Dimensions